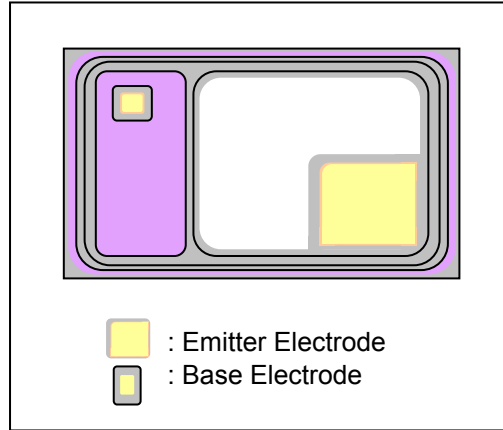


1. Structure

- 1.1 Chip Size : 0.62mm X 0.42mm
- 1.2 Chip thickness : $220 \pm 30 \mu\text{m}$
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Emitter : $160 \mu\text{m}$
 - Base : $60 \mu\text{m} \times 60 \mu\text{m}$



2. Electro-Optical Characteristics

(Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Peak Sensing Wavelength	λ_p		880		nm	
Spectrum Sensitivity	λ	500~1,050			nm	

*Parallel light of 1,000lux illumination is applied by a tungsten lamp of 2856K.

3. Guaranteed Probed Electrical Characteristics

(Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Voltage	V_{CEO}	70			V	$I_C=100\mu\text{A}$
E-B Voltage	V_{EBO}	6			V	$I_E=100\mu\text{A}$
E-C Voltage	V_{ECO}	7			V	$I_E=10\mu\text{A}$
C-E Leakage Current	I_{CEO}			50	nA	$V_{CE}=20\text{V}$
C-E Saturation Voltage	V_{CES}			0.2	V	$I_C=2\text{mA}$, $I_B=100\mu\text{A}$
Rise/Fall Time	t_r/t_f	15/15(Typ)			us	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$, RL-1000 Ω
DC Current Gain	h_{FE}	1300		2,000	-	$V_{CE}=5\text{V}$, $I_C=2\text{mA}$

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